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November 2018

FQB8P10 — P-Channel QFET<sup>®</sup> MOSFET

## FQB8P10

## P-Channel QFET<sup>®</sup> MOSFET

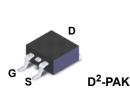
#### -100 V, -8.0 A, 530 mΩ

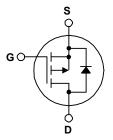
#### Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### Features

- -8.0 A, -100 V,  $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$  = 530 m $\Omega$  (Max.) @ V\_{GS} = -10 V,  $\mathsf{I}_\mathsf{D}$  = -4.0 A
- Low Gate Charge (Typ. 12 nC)
- Low Crss (Typ. 30 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





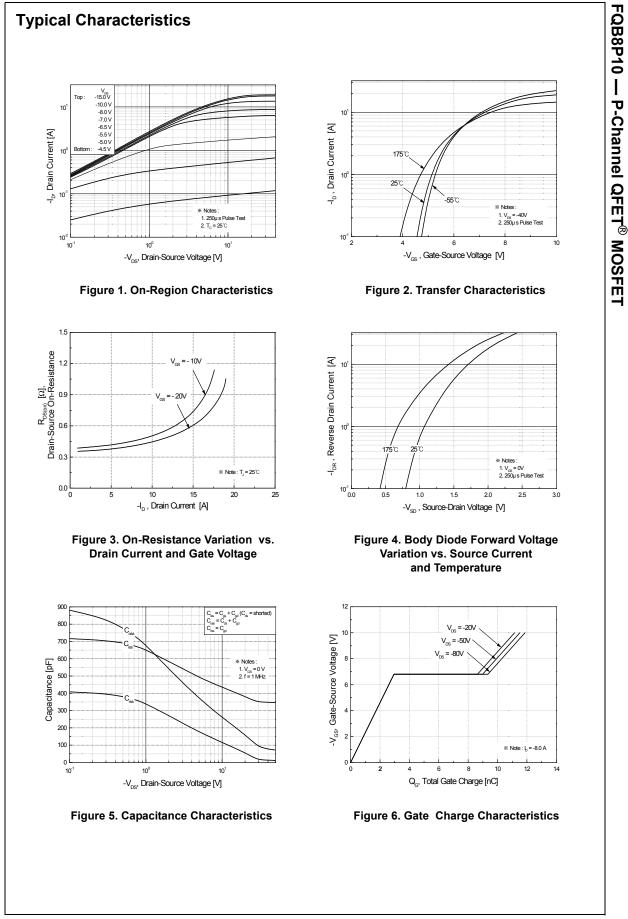
#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

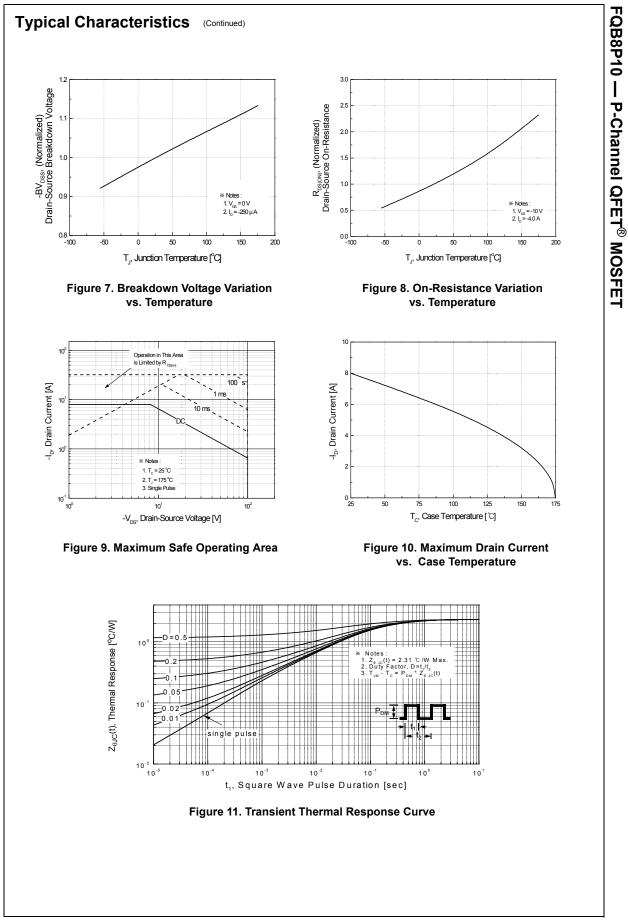
Symbol	Parameter		FQB8P10TM	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		-100	V	
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )		-8.0	A	
	- Continuous (T <sub>C</sub> = 100°C)		-5.7	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-32	Α	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	150	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	-8.0	А	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	6.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note		-6.0	V/ns	
P <sub>D</sub>	Power Dissipation $(T_A = 25^{\circ}C)^{*}$		3.75	W	
	Power Dissipation $(T_C = 25^{\circ}C)$		65	W	
	- Derate above 25°C		0.43	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C	
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds.		300	°C	

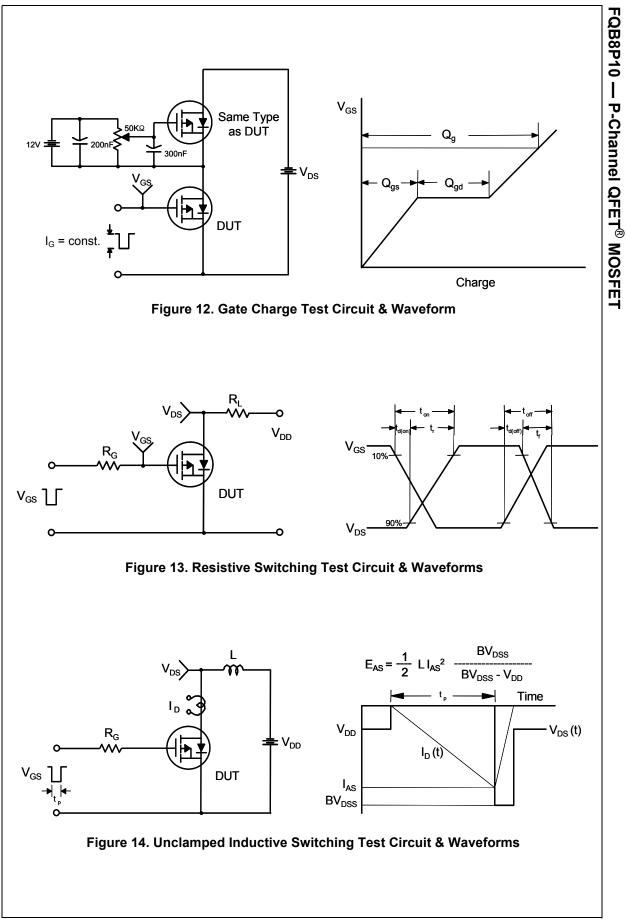
### **Thermal Characteristics**

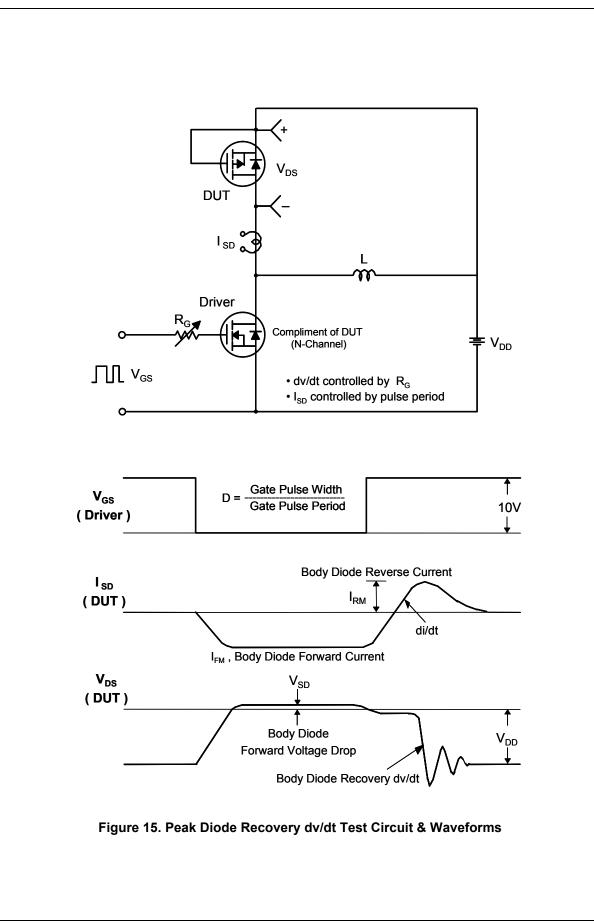
Symbol	Parameter	FQB8P10TM	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.31	
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	°C/W
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	40	

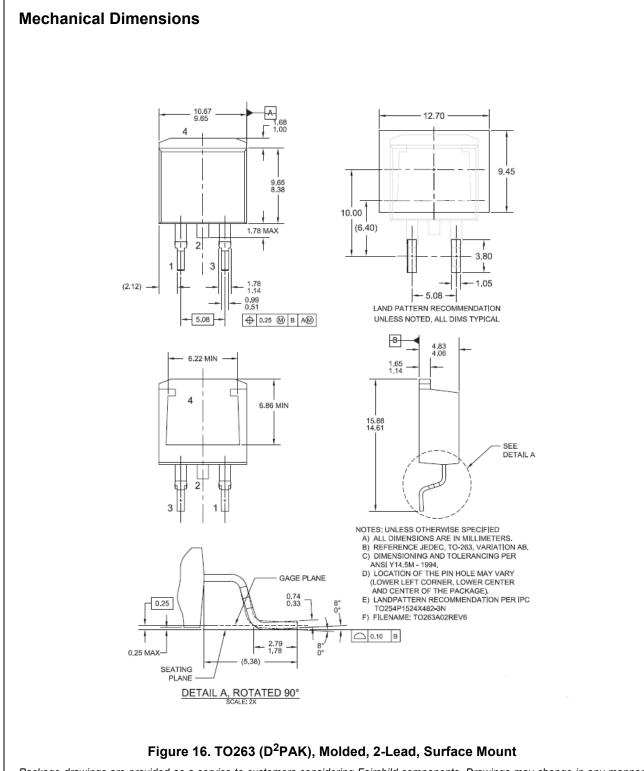
Part Number FQB8P10TM		ber Top Mark		kage Packing Method Reel		Size	Tape Width		Quantity	
		FQB8P10	D <sup>2</sup> -P	PAK	Tape and Reel 33		mm	24 mr	n	800 units
lectric	cal Cha	racteristics	T <sub>C</sub> = 25°C	unless ot	nerwise noted.					
Symbol		Parameter			Test Conditions		Min.	Тур.	Max	Unit
Off Cha	aracterist	ics								
3V <sub>DSS</sub>	Drain-Source Breakdown Voltage		V <sub>GS</sub> =	0 V, I <sub>D</sub> = -250 μA		-100			V	
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient		$I_D$ = -250 µA, Referenced to 25°C				-0.1		V/°C	
DSS	Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward		ant.	V <sub>DS</sub> = -100 V, V <sub>GS</sub> = 0 V				-1	μA	
			V <sub>DS</sub> = -80 V, T <sub>C</sub> = 150°C				-10	μA		
GSSF			$V_{GS}$ = -30 V, $V_{DS}$ = 0 V					-100	nA	
GSSR	Gate-Bod	y Leakage Current, I	Reverse	$V_{GS}$ =	30 V, V <sub>DS</sub> = 0 V				100	nA
On Cha	racterist	ics								
V <sub>GS(th)</sub>		shold Voltage		V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA		-2.0		-4.0	V
R <sub>DS(on)</sub>	Static Dra On-Resist				-10 V, I <sub>D</sub> = -4.0 A			0.41	0.53	Ω
JFS	Forward 1	ransconductance		V <sub>DS</sub> =	-40 V, I <sub>D</sub> = -4.0 A			4.3		S
Ciss Coss Crss	Input Cap Output Ca			V <sub>DS</sub> = f = 1.0	-25 V, V <sub>GS</sub> = 0 V, MHz			360 120 30	470 155 40	pF pF pF
rss	Reveise		;					30	40	μr
	-	acteristics						14	20	
d(on)	Turn-On L Turn-On F	Delay Time		$V_{DD}$ = -50 V, I <sub>D</sub> = -8.0 A, R <sub>G</sub> = 25 $\Omega$ (Note 4)			11	30	ns	
r		Delay Time					110 20	230 50	ns	
d(off) f	Turn-Off F	,				(Note 4)		35	80	ns ns
r Q <sub>a</sub>	Total Gate				00.)/ 1 0.0.4			12	15	nC
×g ⊋ <sub>gs</sub>		rce Charge		V <sub>DS</sub> = V <sub>GS</sub> =	-80 V, I <sub>D</sub> = -8.0 A, -10 V			3.0		nC
<sub>⊐gs</sub> ⊋ <sub>gd</sub>	Gate-Drai	0		•GS -		(Note 4)		6.4		nC
gu										
Drain-S	ource Di	ode Characteri	stics an	d Max	cimum Ratings					
S	Maximum	Continuous Drain-S	ource Dio	de Forw	ard Current				-8.0	А
SM	Maximum	Pulsed Drain-Sourc	rce Diode Forward Current				-32	Α		
/ <sub>SD</sub>	Drain-Sou	Irce Diode Forward	/oltage		0 V, I <sub>S</sub> = -8.0 A				-4.0	V
rr		Recovery Time			0 V, I <sub>S</sub> = -8.0 A,			98		ns
ל <sup>ער</sup>	Reverse F	Recovery Charge		dl <sub>F</sub> / d	t = 100 A/μs			0.35		μC
L = 3.5 mH,	I <sub>AS</sub> = -8.0 A, V <sub>I</sub>	Ith limited by maximum jun <sub>DD</sub> = -25 V, R <sub>G</sub> = 25 Ω, star Is , V <sub>DD</sub> ≤ BV <sub>DSS</sub> starting 1	ting $T_J = 25^{\circ}$							











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P-Channel QFET<sup>®</sup> MOSFET



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